

/ Descriptions

KF \$() - = E GE Silicon NPN transistor in a TO-126F Plastic Package.

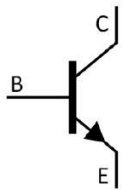
/ Features

Low $V_{CE(sat)}$, high current and high f_T , excellent linearity of h_{FE} , fast switching time.

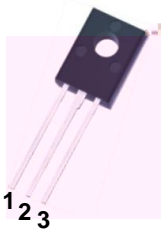
/ Applications

Relay drivers, high-speed inverters, general high-current switching applications.

/ Equivalent Circuit



/ Pinning



PIN1 Emitter PIN 2 Collector PIN 3 Base

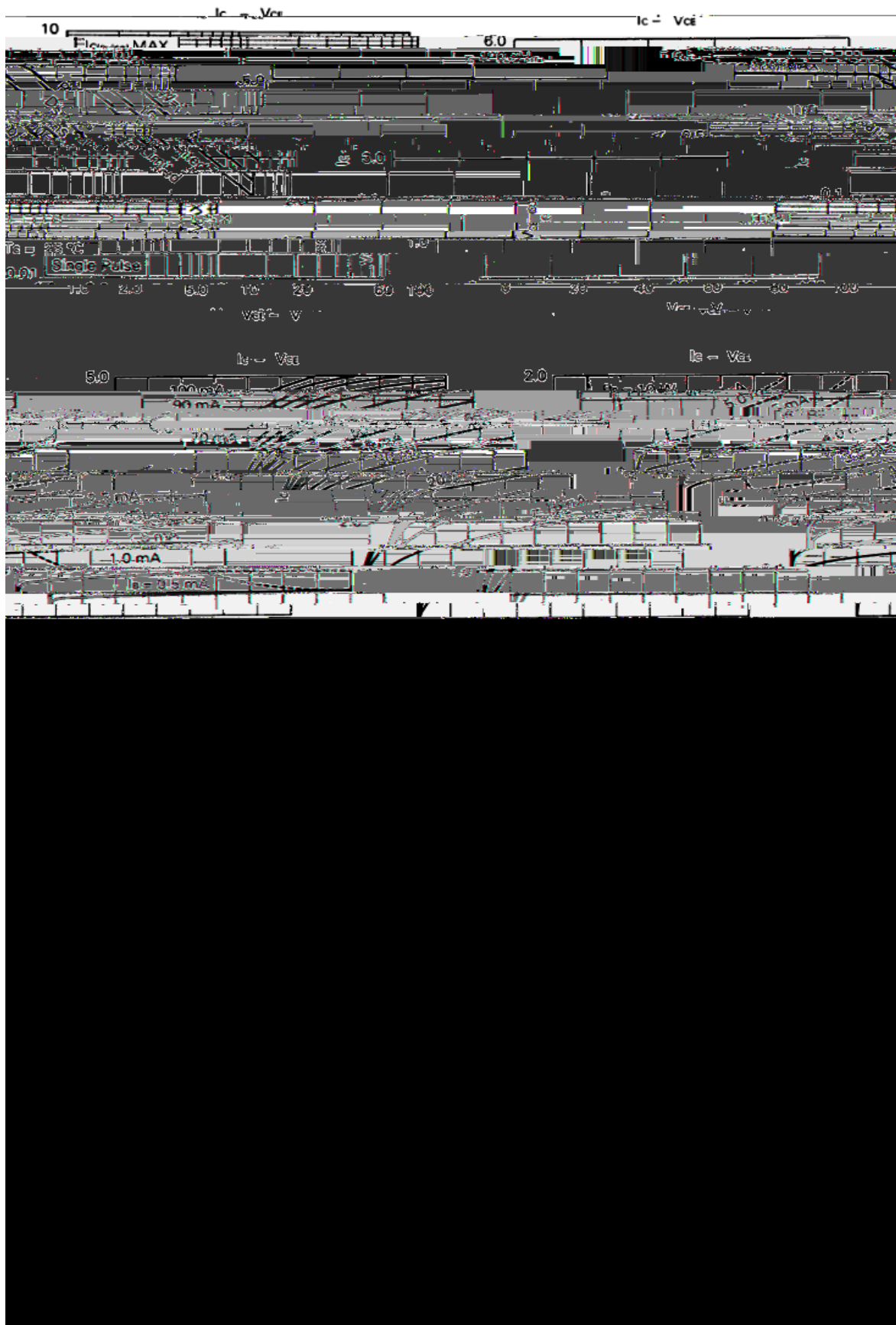
/ h_{FE} Classifications & Marking

h_{FE} Classifications Symbol	M	L	K
h_{FE} Range	100 200	160 320	200 400

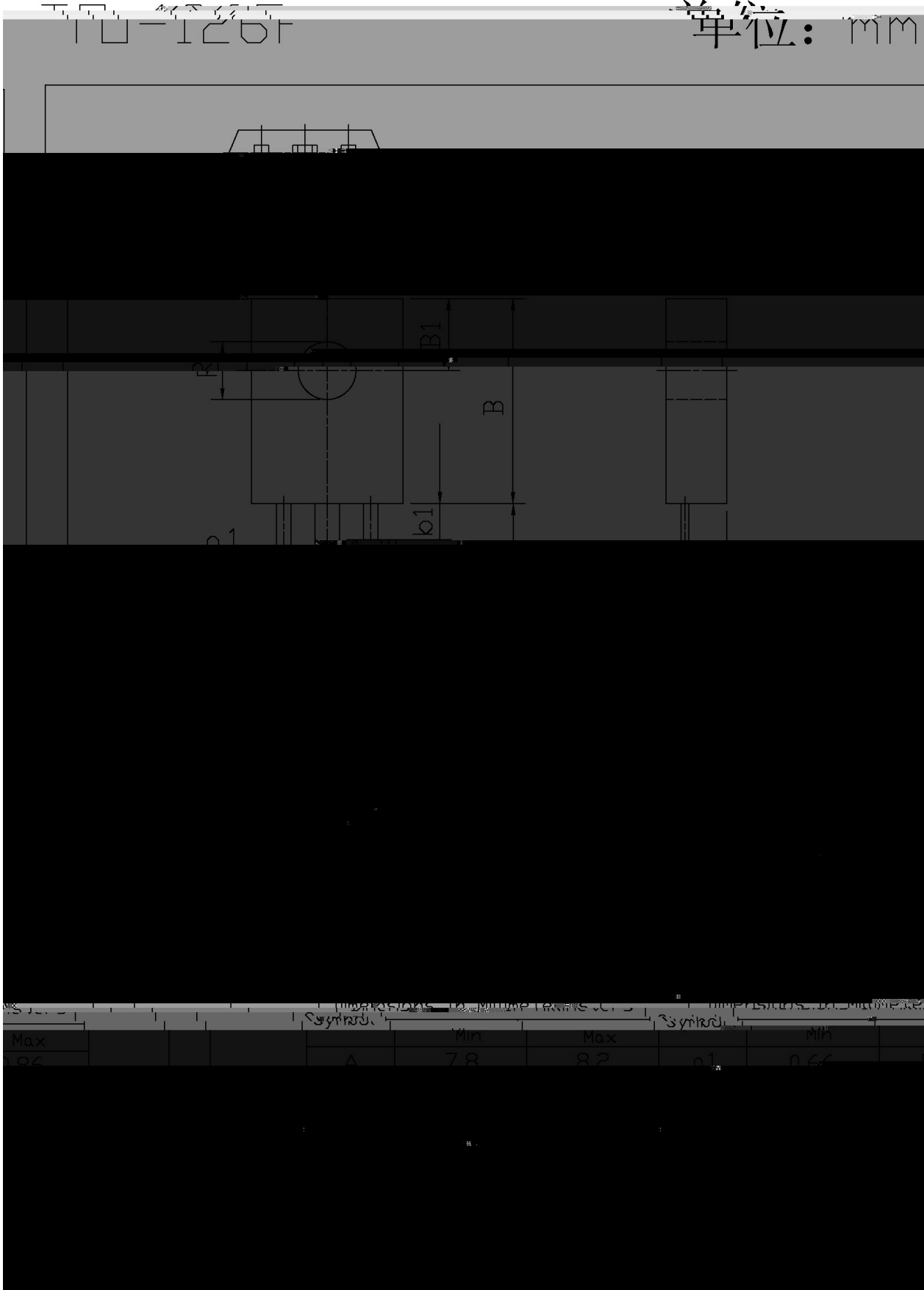
Parameter	Symbol	Rating	Unit
Collector to Base Voltage	V_{CBO}	60	V
Collector to Emitter Voltage	V_{CEO}	60	V
Emitter to Base Voltage	V_{EBO}	7.0	V
Collector Current - Continuous	I_C	3.0	A
Collector Power Dissipation	P_C	2.0	W
Collector Power Dissipation	$P_C(T_c=125^\circ C)$	10	W
Junction Temperature	T_j	150	
Storage Temperature Range	T_{stg}	-55 150	

Parameter	Symbol	Test Conditions	Min	Typ	Max	Unit	Á
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/ Electrical Characteristic Curve

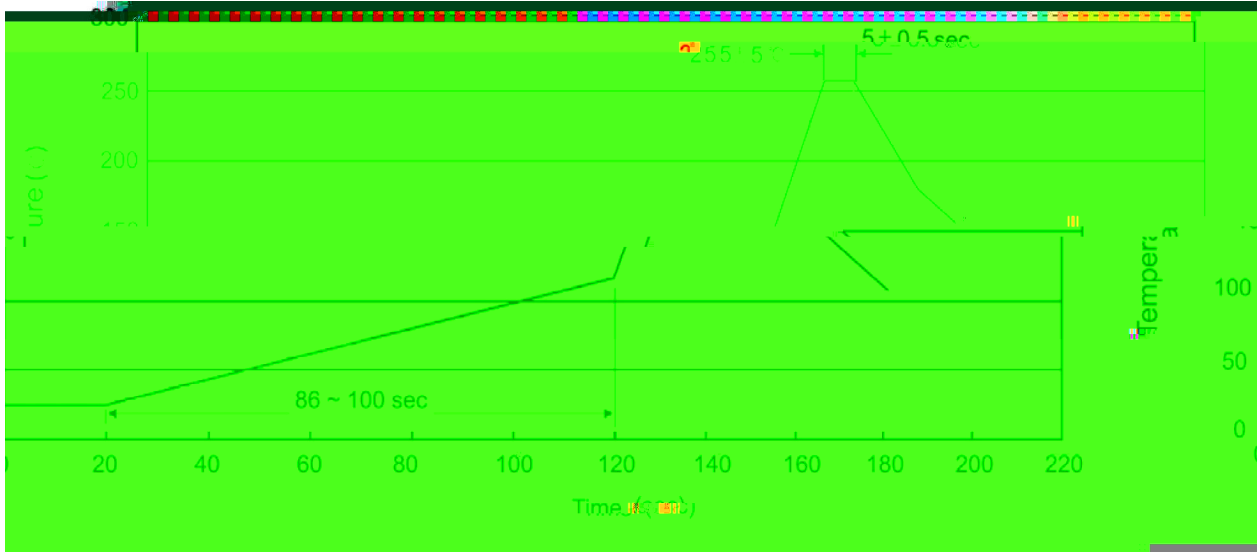


/ Package Dimensions



Symbol	Min	Max	Symbol	Min	Max
b1	7.8	8.2	b2	0.6	0.6

() / Temperature Profile for Dip Soldering(Pb-Free)



Note:

- | | | | | | |
|---|--------|-----|------------|----------|---|
| 1 | 25 | 150 | 60 | 90sec; | 1.Preheating:25~150 , Time:60~90sec. |
| 2 | 255..5 | | 5..0.5sec; | | 2.Peak Temp.:255..5 , Duration:5..0.5sec. |
| 3 | | | 2 | 10 /sec. | 3. Cooling Speed: 2~10 /sec. |

/ Resistance to Soldering Heat Test Conditions

270..5 10..1 sec. Temp.:270±5 Time:10±1 sec

/ Packaging SPEC.

/ BULK

Package Type 封装形式	Units 包装数量					Dimension 包装尺寸 (unit: mm ³)
	Units/Tube 只/套管	Tubes/Inner Box 套管/盒	Units/Inner Box 只/盒	Inner Boxes/Outer Box 盒/箱	Units/Outer Box 只/箱	